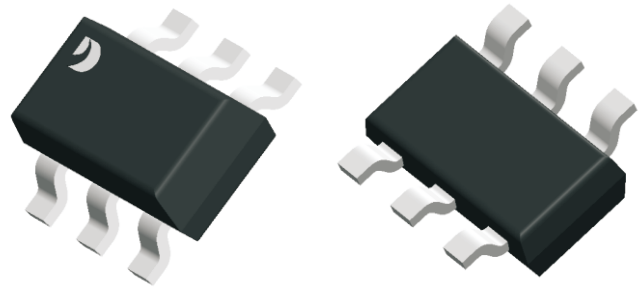


N-Channel MOSFET

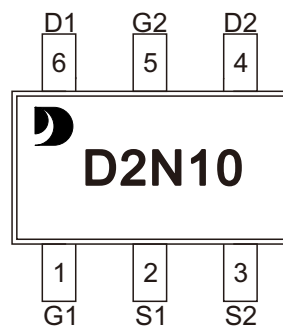
Features

- 100V,2A
- Advanced Trench Technolog
- Provide Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

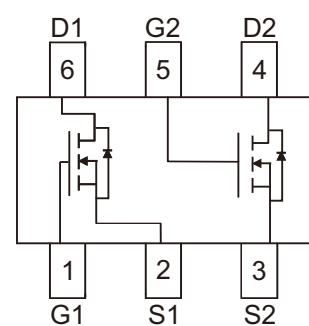


Application

- Load Switch
- PWM Application
- Power management



Marking and pin Assignment



DNM2N10A

Absolute Maximum Ratings (TA=25°C unless otherwise specified)

Symbol	Parameter	Max	Units
V_{DSS}	Drain-Source Voltage	100	V
V_{GSS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Current	2	A
P_D	Power Dissipation Steady State	1.5	W
$R_{\theta JA}$	Thermal Resistance, Junction to Case	80	°CW
T_j, T_{stg}	Operating and Storage Temperature Range	-55~+150	°C



Electrical Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	100			V
Static Drain-Source On-Resistance ^(Note1)	R _{DS(on)}	V _{GS} =10V, I _D =1A		220	320	mΩ
		V _{GS} =4.5V, I _D =1A		300	450	mΩ
Gate Threshold Voltage ^(Note1)	V _{GS(th)}	V _{GS} =V _{DS} , I _D =250uA	0.8	1.2	1.6	V
Gate-to-Source Leakage Current	I _{DSS}	V _{DS} =80V, V _{GS} =0V			1	uA
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =± 20V			± 100	nA
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V f=1.0MHz		362		pF
Output Capacitance	C _{oss}			10.5		pF
Reverse Transfer Capacitance	C _{rss}			6.8		pF
Total Gate Charge	Q _g				3.5	
Gate-Source Charge	Q _{gs}	V _{DS} =50V, V _{GS} =10V I _D =1A		0.5		nC
Gate-Drain("Miller") Charge	Q _{gd}			0.7		nC
Turn-on Delay Time	t _{d(on)}	V _{DD} =50V, V _{GS} =10V I _D =2A R _G =2Ω		9.1		ns
Turn-on Rise Time	t _r			1.8		ns
Turn-off Delay Time	t _{d(off)}			8.3		ns
Turn-off Fall Time	t _f			7.6		ns

1. Pulse test ;Pulse width ≤ 300us, duty cycle ≤ 2%



Typical Electrical and Thermal Characteristics

Fig 1 Output Characteristics

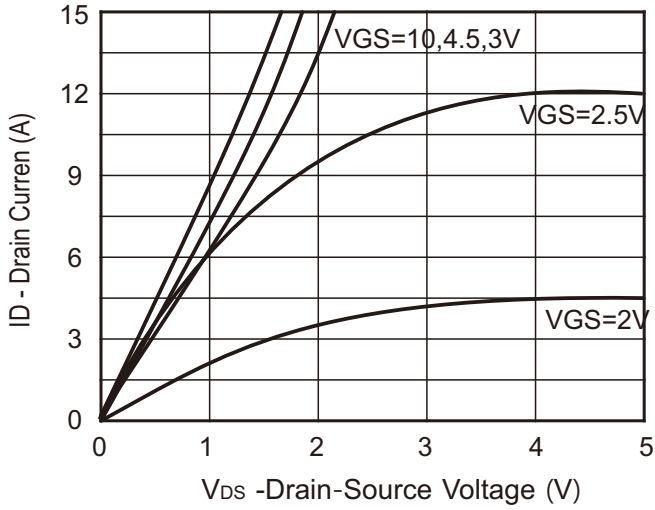


Fig 2 Thermal Characteristics

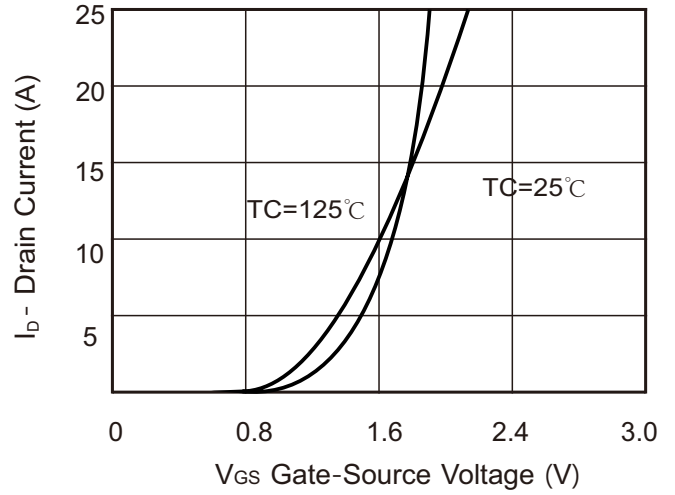


Fig 6 Source- Drain Diode Forward

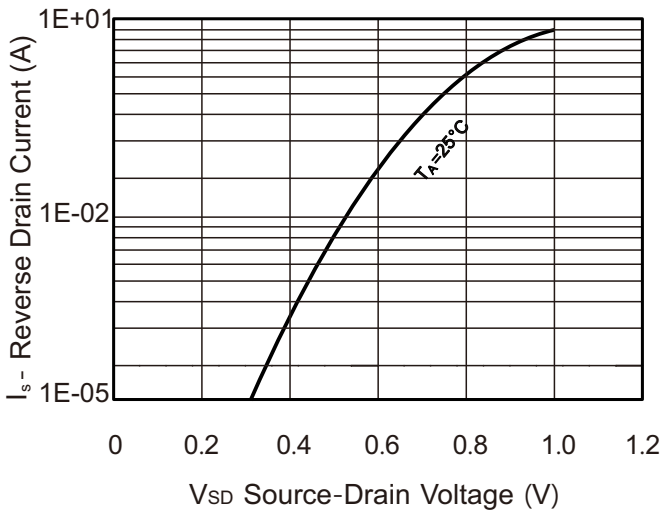
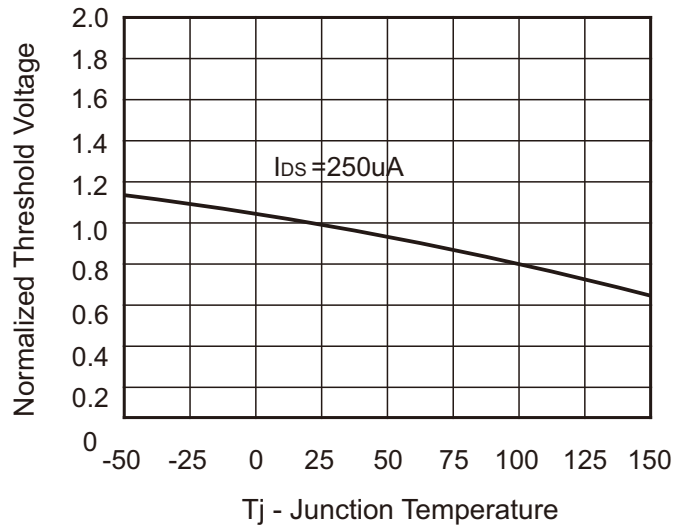


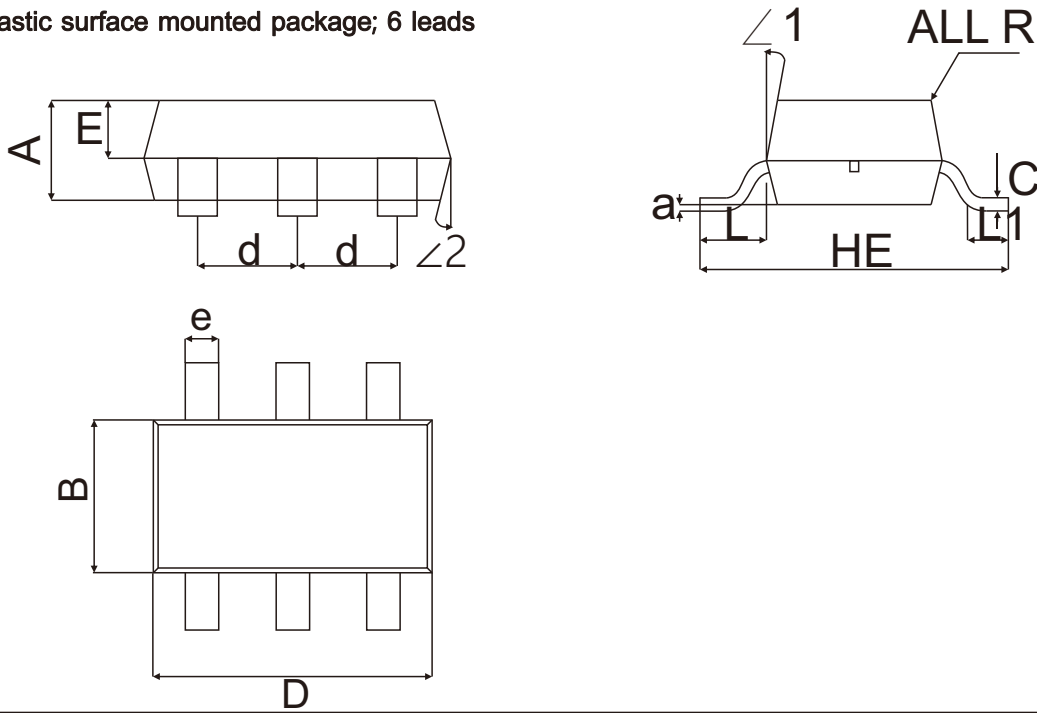
Fig 4 Gate Threshold Characteristics





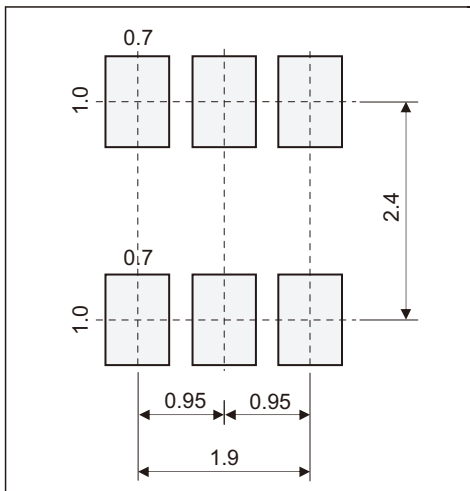
PACKAGE OUTLINE

Plastic surface mounted package; 6 leads



Unit		A	B	C	HE	D	d	E	e	L	L1	a	R	∠1	∠2
mm	max	1.05	1.80	0.20	2.90	3.12	1.00	0.65	0.40	0.70	0.60	0.2 (ref)	R0.1 (ref)	12°	10°
	typ	0.95	1.60	0.15	2.80	2.92	0.95	0.55	0.35	0.60	/				
	min	0.85	1.40	0.10	2.70	2.72	0.90	0.45	0.30	0.50	0.20				
mil	max	41	71	8	114	123	39	26	16	28	24	8 (ref)	R4 (ref)	12°	10°
	typ	37	63	6	110	115	37	22	14	24	/				
	min	33	55	4	106	107	35	18	12	20	8				

The recommended mounting pad size



Marking

Type number	Marking code
DNM2N10A	D2N10